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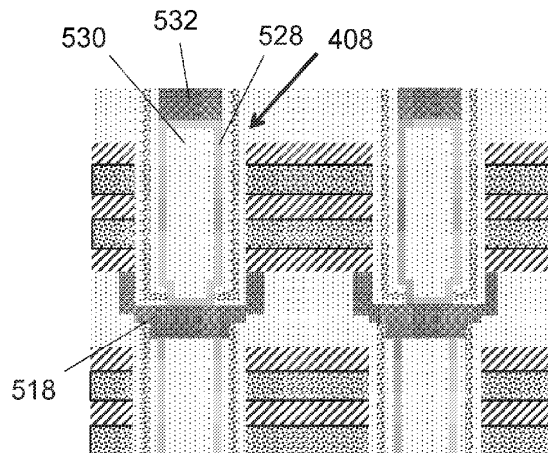


FIG. 5F

(57) Abstract: Disclosed are three-dimensional memory device architectures and fabrication methods. The memory device includes a substrate (202) having a first layer stack (204) on it. The first layer stack (204) includes alternating conductor and insulator layers (206, 208). A second layer stack (402) is disposed over the first layer stack (202) where the second layer stack (402) also includes alternating conductor and insulator layers (404, 406). One or more vertical structures (210) extend through the first layers stack (202). A conductive material (518) is disposed on a top surface of the one or more vertical structures (210). One or more second vertical structures (408) extend through the second layer stack (402) and through a portion of the conductive material (518).

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WO 2020/034084 A1

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